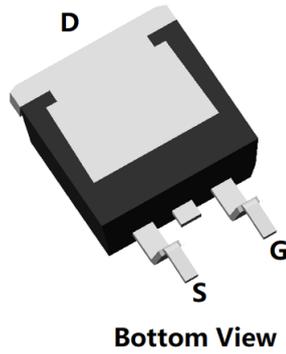
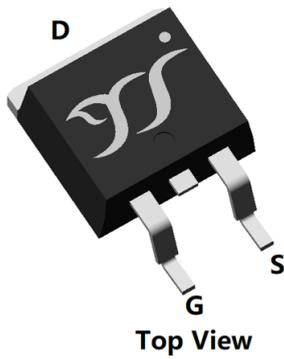
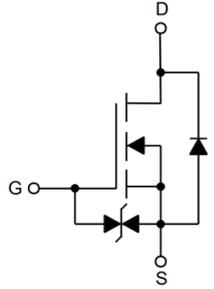


N-Channel Enhancement Mode Field Effect Transistor



TO-263



Product Summary

- V_{DS} 800V
- I_D 22A
- $R_{DS(ON)}$ (at $V_{GS}=10V$) <math>< 190m\Omega</math>
- 100% EAS Tested
- 100% ∇V_{DS} Tested

General Description

- Super Junction High Voltage MOSFET technology
- Ultra Low Gate Charge Cause Lower Driving Requirement
- Low On-resistance and Low Conduction Loss
- Moisture Sensitivity Level 1
- Epoxy Meets UL 94 V-0 Flammability Rating
- Halogen Free

Applications

- Switching Mode Power Supplies (SMPS)
- PWM Motor Controls
- LED Lighting
- Adapter

Limiting Values

Parameter	Conditions	Symbol	Min	Max	Unit	
Drain-source Voltage		V_{DS}	-	800	V	
Gate-source Voltage		V_{GS}	-20	20	V	
Continuous Drain Current (Note 1,2)	Steady-State	I_D	$T_A=25^\circ C, V_{GS}=10V$	-	2.4	A
			$T_A=100^\circ C, V_{GS}=10V$	-	1.5	
Continuous Drain Current (Note 1,3)	Steady-State		$T_C=25^\circ C, V_{GS}=10V$	-	22	
			$T_C=100^\circ C, V_{GS}=10V$	-	13.9	
Pulsed Drain Current	$T_C=25^\circ C, t_p \le 10\mu s$	I_{DM}	-	65		
Maximum Body-Diode Continuous Current	$T_C=25^\circ C$	I_S		22		
Maximum Body-Diode Pulsed Current	$T_C=25^\circ C, t_p \le 10\mu s$	I_{SM}	-	65		
Avalanche Energy (non-repetitive)	$T_J=25^\circ C, V_G=10V, R_G=25\Omega, L=30mH, I_{AS}=6.3A$	EAS	-	595.3	mJ	
Total Power Dissipation (Note 1,2)	Steady-State	P_D	$T_A=25^\circ C$	-	3.1	W
			$T_A=100^\circ C$	-	1.2	
Total Power Dissipation (Note 1,3)	Steady-State		$T_C=25^\circ C$	-	245	
			$T_C=100^\circ C$	-	98	
MOSFET dv/dt Ruggedness	$T_J=25^\circ C, V_{DS}=0 \dots 400V, I_D \le 21A, R_g=1\Omega$	dv/dt	-	128	V/ns	
Reverse Diode dv/dt	$T_J=25^\circ C, V_{DS}=0 \dots 400V, I_D \le 21A, di/dt=100A/\mu s$	dv/dt	-	53	V/ns	
Maximum Diode Commutation Speed	$T_J=25^\circ C, V_{DS}=0 \dots 400V, I_D \le 21A, R_g=1\Omega$	dif/dt	-	1500	A/ μs	
Junction and Storage Temperature Range		T_J, T_{STG}	-55	150	$^\circ C$	

Thermal Resistance

Parameter	Symbol	Typ	Max	Units
Thermal Resistance Junction-to-Ambient (Note 2)	$R_{\theta JA}$	-	40	$^\circ C/W$
Thermal Resistance Junction-to-Case	$R_{\theta JC}$	-	0.51	

Ordering Information (Example)

PREFERRED P/N	PACKING CODE	Marking	MINIMUM PACKAGE(pcs)	INNER BOX QUANTITY(pcs)	OUTER CARTON QUANTITY(pcs)	DELIVERY MODE
YJB190C80BZJ	F2	YJB190C80BZ	800	/	4000	13" reel



YJB190C80BZJ

■ Electrical Characteristics

Parameter	Symbol	Conditions	Min	Typ	Max	Units
Static Parameter						
Drain-Source Breakdown Voltage	BV_{DSS}	$V_{GS}=0V, I_D=250\mu A, T_j=25^\circ C$	800	-	-	V
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS}=800V, V_{GS}=0V, T_j=25^\circ C$	-	-	1	μA
		$V_{DS}=800V, V_{GS}=0V, T_j=125^\circ C$	-	-	100	
Gate-Source Leakage Current	I_{GSS}	$V_{GS}=\pm 20V, V_{DS}=0V, T_j=25^\circ C$	-	-	± 10	μA
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}, I_D=250\mu A, T_j=25^\circ C$	3	3.8	4.6	V
Static Drain-Source On-Resistance	$R_{DS(on)}$	$V_{GS}=10V, I_D=12A, T_j=25^\circ C$	-	153	190	$m\Omega$
		$V_{GS}=10V, I_D=12A, T_j=150^\circ C$	-	405	503	$m\Omega$
Diode Forward Voltage	V_{SD}	$I_S=22A, V_{GS}=0V, T_j=25^\circ C$	-	0.86	1.2	V
Gate Resistance	R_G	$f=1MHz, T_j=25^\circ C$	-	4	-	Ω
Dynamic Parameters						
Input Capacitance	C_{iss}	$V_{DS}=400V, V_{GS}=0V, f=1MHz, T_j=25^\circ C$	-	2944	-	pF
Output Capacitance	C_{oss}		-	44.3	-	
Reverse Transfer Capacitance	C_{rss}		-	1.8	-	
Effective output capacitance, energy related	$C_{o(er)}$	$V_{DS}=0\dots 400V, V_{GS}=0V, f=1MHz, T_j=25^\circ C$	-	72	-	pF
Effective output capacitance, time related	$C_{o(tr)}$		-	328	-	
Switching Parameters						
Total Gate Charge	Q_g	$V_{GS}=10V, V_{DS}=400V, I_D=22A, T_j=25^\circ C$	-	62	-	nC
Gate-Source Charge	Q_{gs}		-	16.7	-	
Gate-Drain Charge	Q_{gd}		-	23.5	-	
Reverse Recovery Charge	Q_{rr}	$I_F=22A, di/dt=100A/\mu s, V_{GS}=0V, V_R=400V, T_j=25^\circ C$	-	8.1	-	μC
Reverse Recovery Time	t_{rr}		-	418	-	ns
Peak Reverse Recovery Current	I_{rrm}		-	33.8	-	A
Turn-on Delay Time	$t_{D(on)}$	$V_{GS}=10V, V_{DS}=400V, I_D=22A, R_{GEN}=3\Omega, T_j=25^\circ C$	-	84	-	ns
Turn-on Rise Time	t_r		-	37	-	
Turn-off Delay Time	$t_{D(off)}$		-	50	-	
Turn-off Fall Time	t_f		-	14	-	

Note:

- The entire application environment impacts the thermal resistance values shown, they are not constants and are only valid for the particular conditions noted.
- The value of $R_{\theta JA}$ is measured with the device mounted on the 40mm*40mm*1.1mm single layer FR-4 PCB board with 1 in² pad of 2oz. Copper, in the still air environment with $T_A=25^\circ C$. The maximum allowed junction temperature of 150 $^\circ C$. The value in any given application depends on the user's specific board design.
- Thermal resistance from junction to soldering point (on the exposed drain pad).



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Typical Electrical and Thermal Characteristics Diagrams

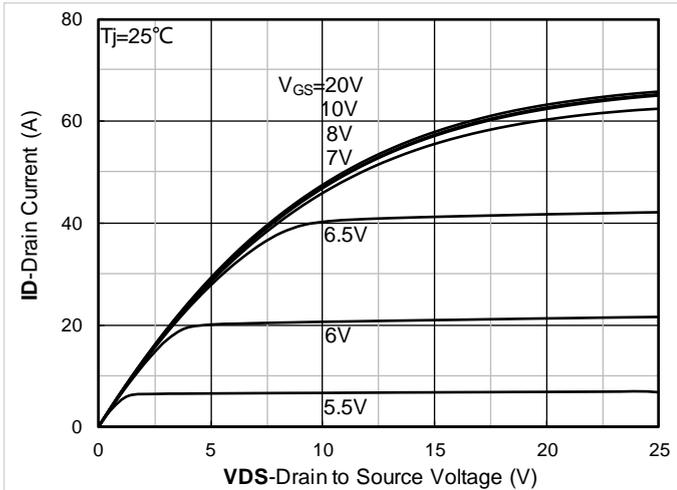


Figure 1. Output Characteristics; typical values

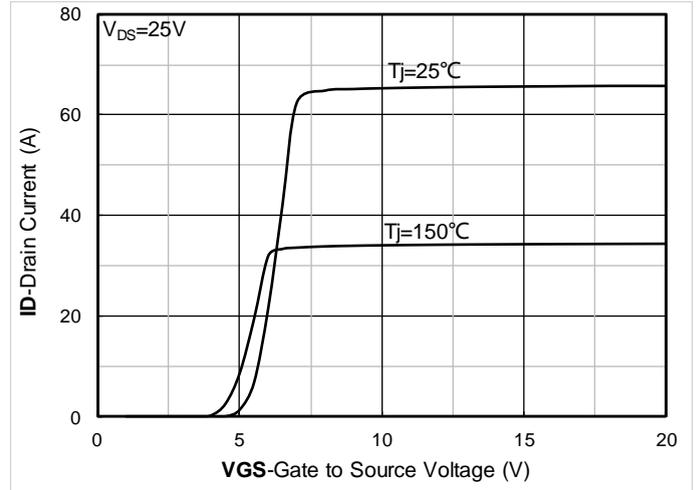


Figure 2. Transfer Characteristics; typical values

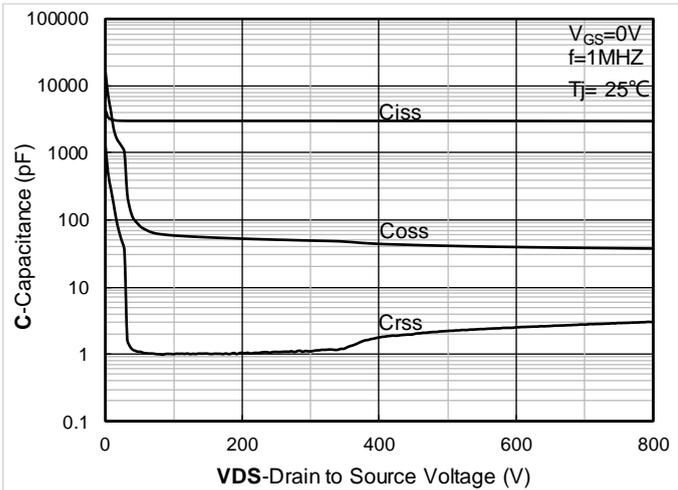


Figure 3. Capacitance Characteristics; typical values

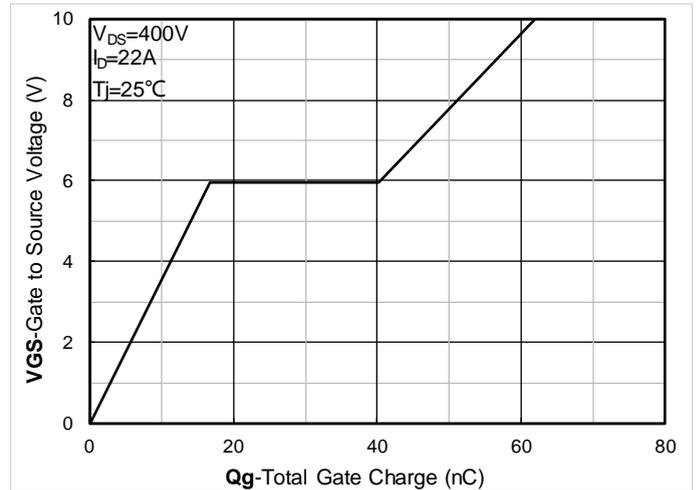


Figure 4. Gate Charge; typical values

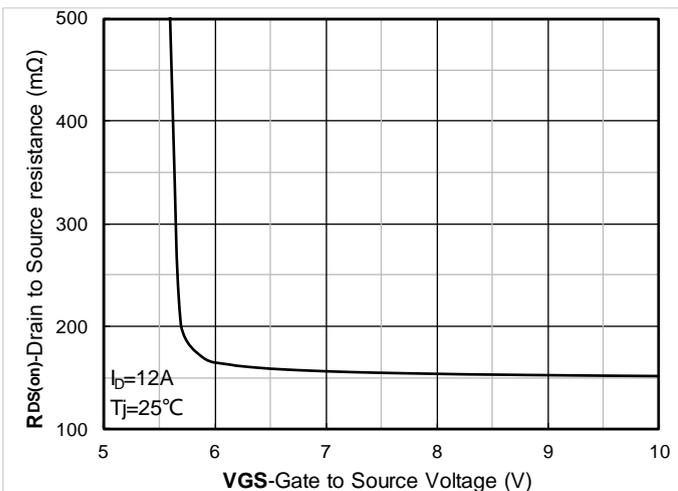


Figure 5. On-Resistance vs. Gate to Source Voltage; typical values

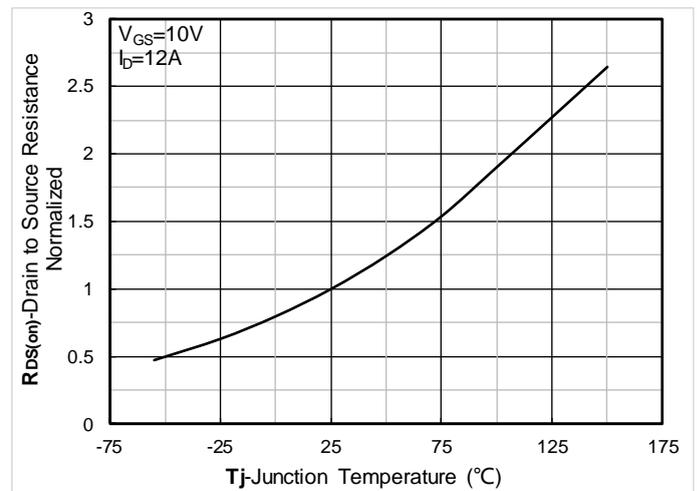


Figure 6. Normalized On-Resistance



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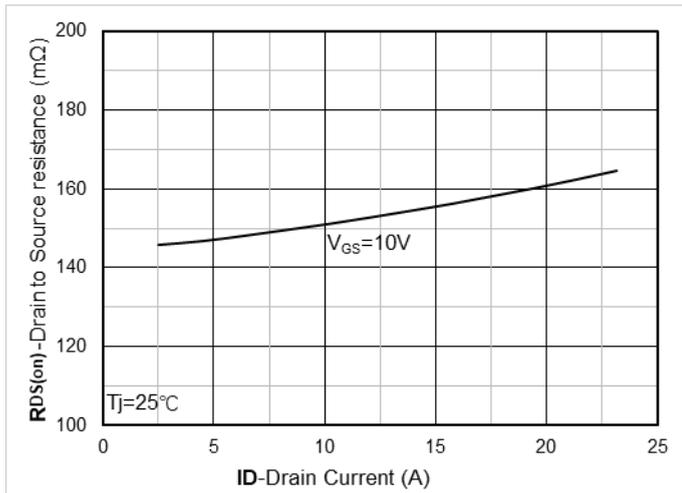


Figure 7. RDS(on) vs. Drain Current; typical values

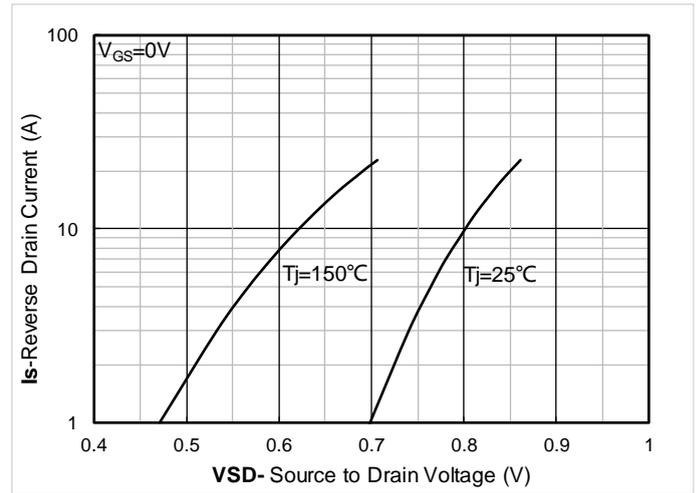


Figure 8. Forward characteristics of reverse diode; typical values

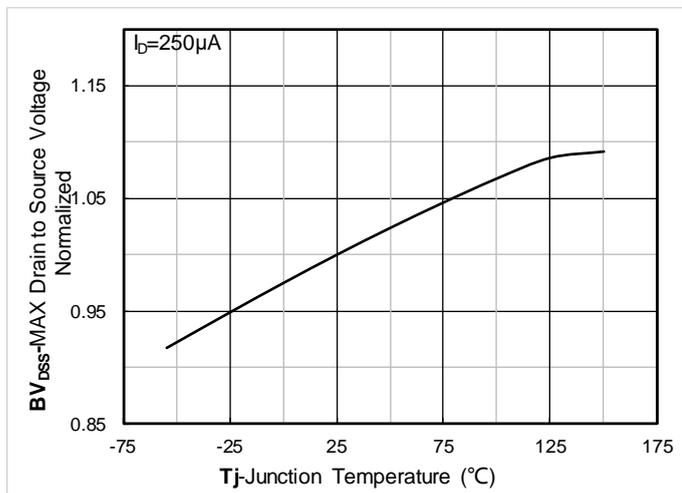


Figure 9. Normalized breakdown voltage

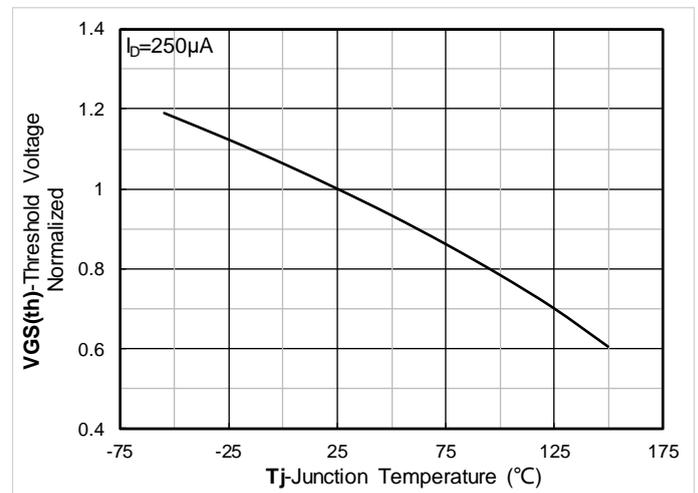


Figure 10. Normalized Threshold voltage

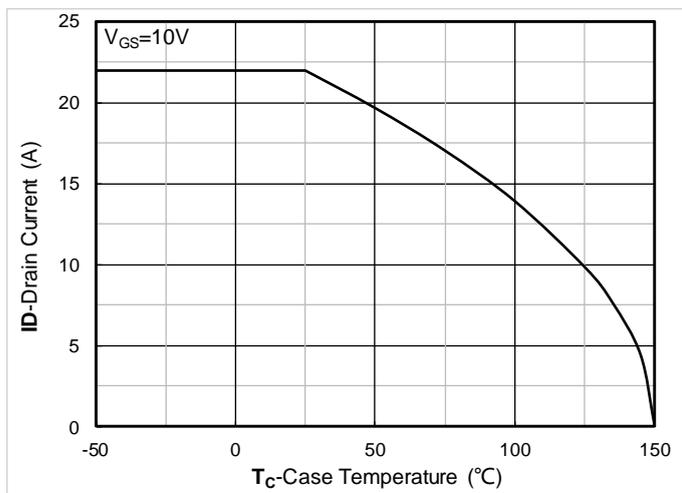


Figure 11. Current dissipation

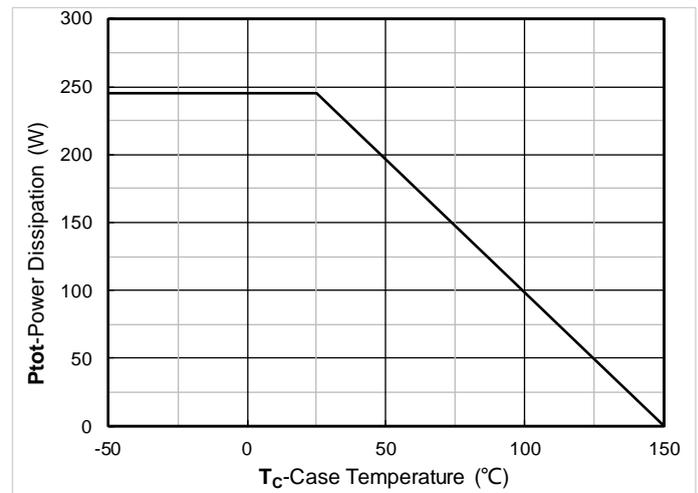


Figure 12. Power dissipation



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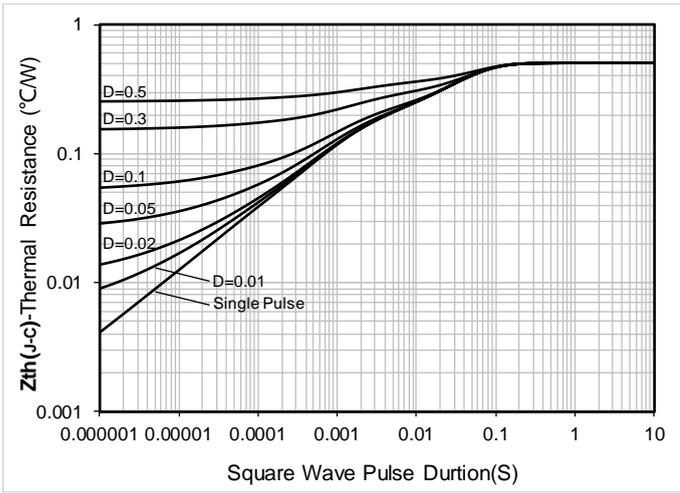


Figure 13. Maximum Transient Thermal Impedance

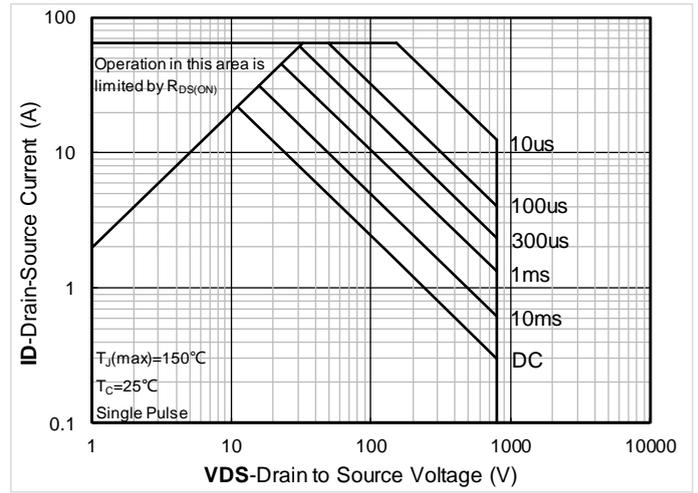


Figure 14. Safe Operation Area

■ Test Circuits & Waveforms

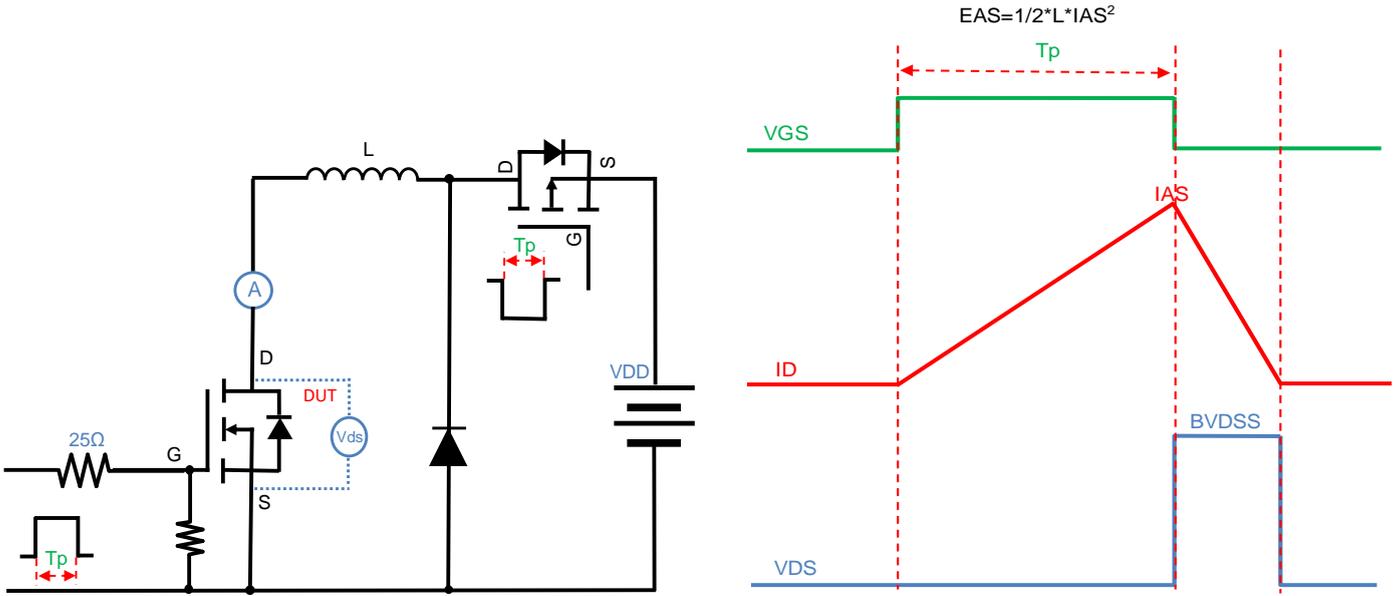


Figure A. Unclamped Inductive Switching (UIS) Test Circuit & Waveform

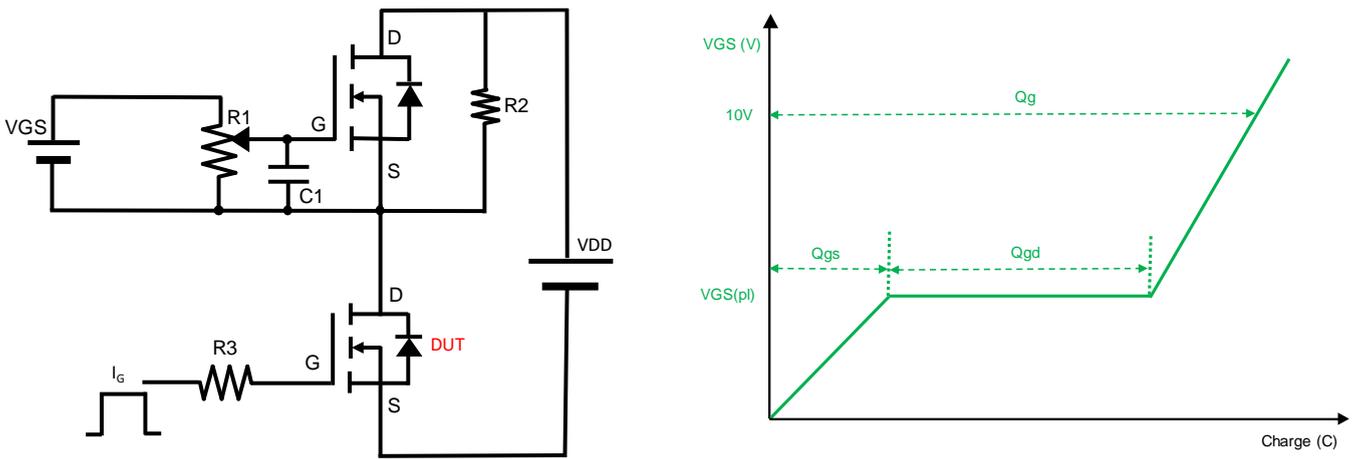


Figure B. Gate Charge Test Circuit & Waveform

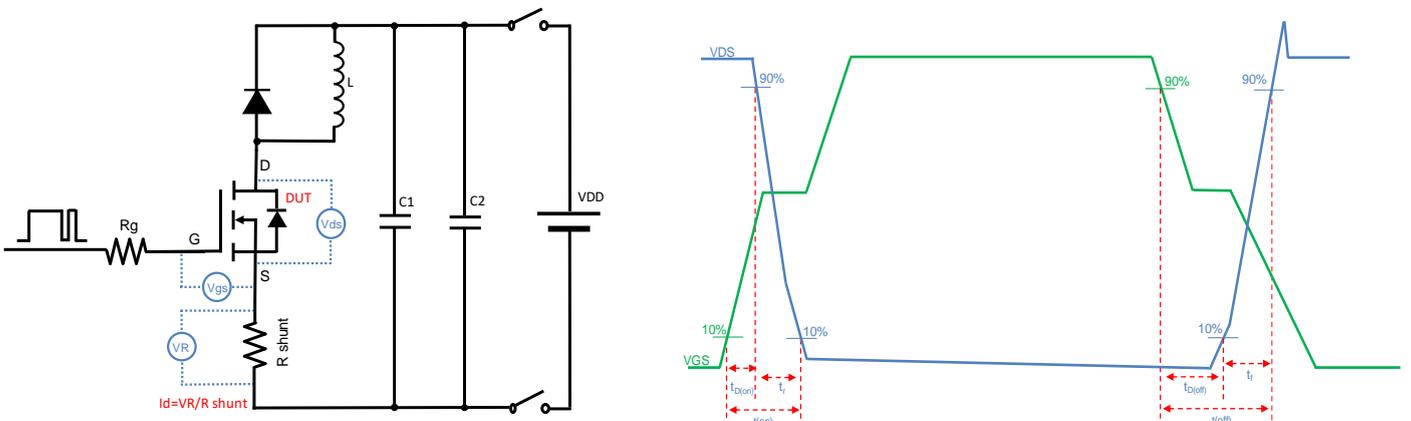


Figure C. Resistive Switching Test Circuit & Waveform

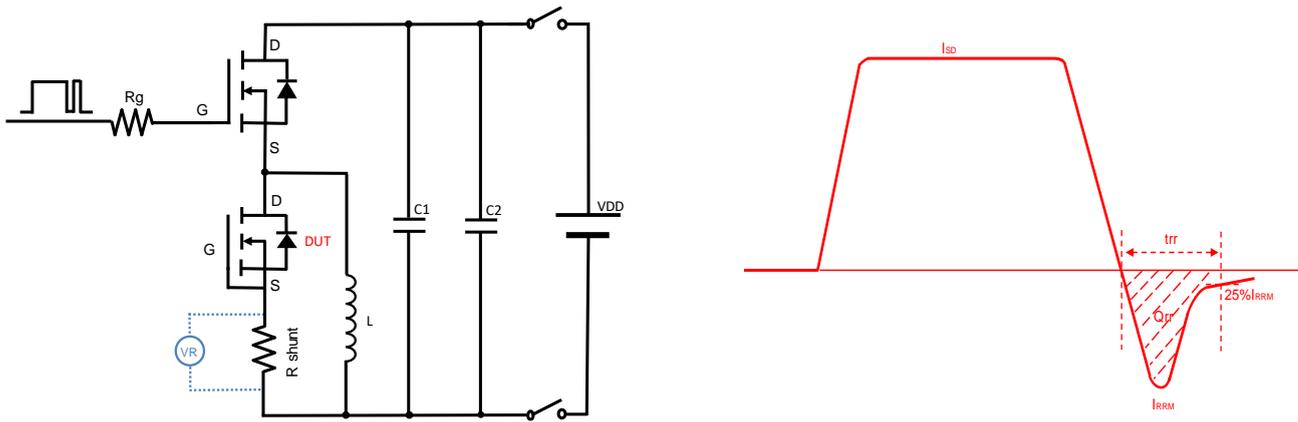
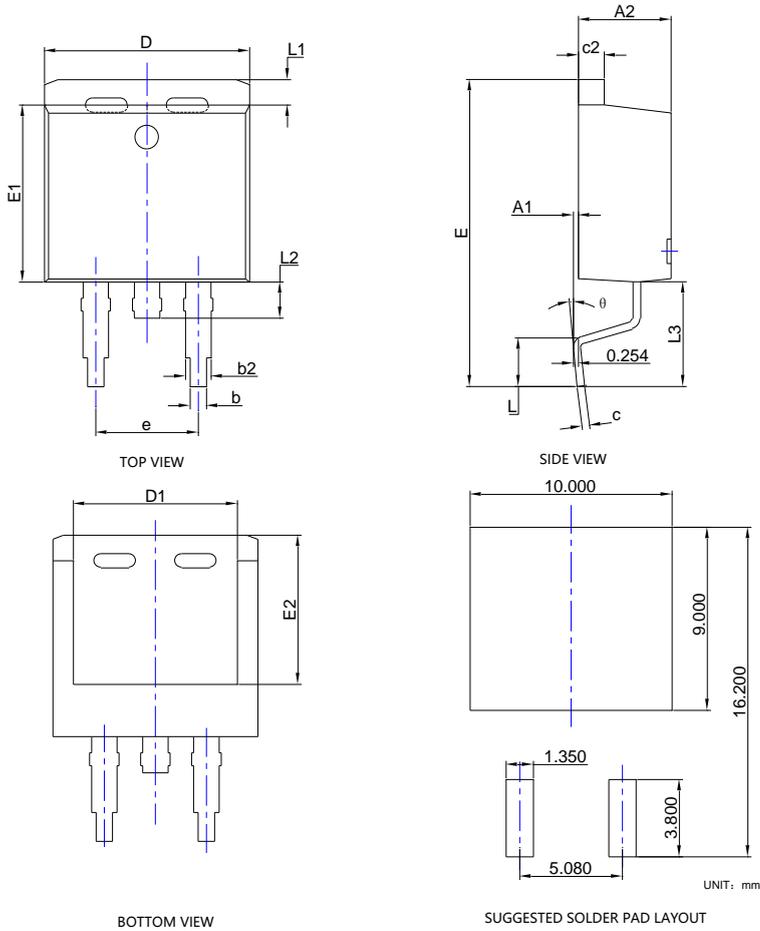


Figure D. Diode Recovery Test Circuit & Waveform



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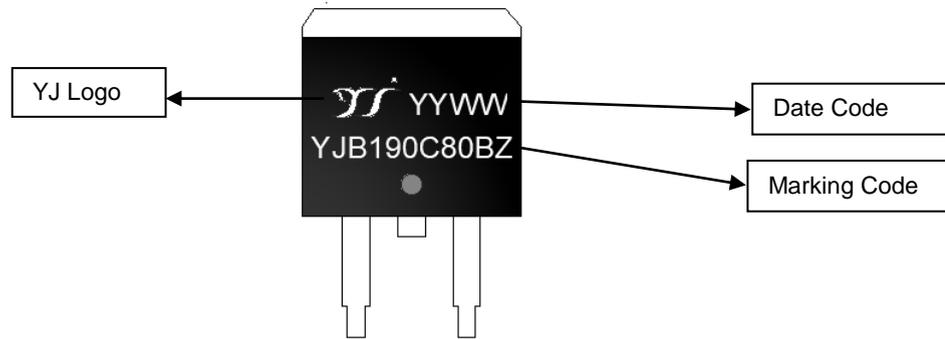
■ TO-263-B Package information



SYMBOL	DIMENSIONS			
	INCHES		MILLIMETER	
	MIN.	MAX.	MIN.	MAX.
A1	0.000	0.010	0.000	0.254
A2	0.160	0.190	4.064	4.826
b	0.020	0.039	0.508	0.991
b2	0.045	0.070	1.143	1.778
c	0.015	0.029	0.381	0.737
c2	0.045	0.065	1.143	1.651
D	0.380	0.420	9.652	10.668
D1	0.245	---	6.223	---
E	0.575	0.625	14.605	15.875
E1	0.330	0.380	8.382	9.652
E2	0.270	---	6.858	---
e	0.200BSC		5.08BSC	
L	0.070	0.110	1.778	2.794
L1	---	0.066	---	1.676
L2	---	0.070	---	1.778
L3	0.188	0.208	4.780	5.280
θ	0°	8°	0°	8°

NOTE:
 1. PACKAGE BODY SIZES EXCLUDE MOLD FLASH AND GATE BURRS.
 2. TOLERANCE 0.1mm UNLESS OTHERWISE SPECIFIED.
 3. THE PAD LAYOUT IS FOR REFERENCE PURPOSES ONLY.

■ Marking Information



Note:

1. All marking is at middle of the product body
2. All marking is in laser printing
3. YJB190C80BZ is marking code, YYWW is date code, "YY" is year, "WW" is week
4. Body color: Black



YJB190C80BZJ

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